## AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions, and listings, of claims in the application.

## **Listing of the Claims**

Claims 1-13 (Canceled)

- 14. (Original) Method of making a sputter target comprising:
- a) providing an Me powder comprising a member selected from groups IVB, VB, VIB and VIII of the periodic table;
  - b) providing Si<sub>3</sub>N<sub>4</sub> powder;
  - c) providing a sintering aid selected from MgO and SiO;
  - d) blending said Me powder, Si<sub>3</sub>N<sub>4</sub> powder and sintering aid to form a blend;
- e) pressure consolidating said blend under heated conditions for a time sufficient to form a consolidated blend having an actual density of greater than 95% of the theoretical density.
- 15. (Original) Method as recited in claim 14 further comprising machining said pressure consolidated blend from said step (e) to final desired shape.
- 16. (Original) Method as recited in claim 14 wherein said blend comprises from about 40 about 80 atomic percent Me, about 60 about 20 atomic percent Si<sub>3</sub>N<sub>4</sub> with said the atomic percent of said Si<sub>3</sub>N<sub>4</sub> and said Me equaling about 100 atomic percent, said sintering aid being MgO present in an amount of between about 0.05-6 weight percent based on the weight of said Si<sub>3</sub>N<sub>4</sub>.
- 17. (Original) Method as recited in claim 16 wherein Me is W.

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- 18. (Original) Method as recited in claim 16 further comprising conducting said pressure consolidating step (e) in an inert gaseous atmosphere.
- 19. (Original) Method as recited in claim 18 wherein said pressure is greater than about 1 atmosphere.
- 20. (Original) Method as recited in claim 19 wherein pressure consolidation is conducted at temperatures of about 900°C-1700°C.